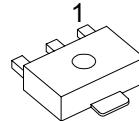
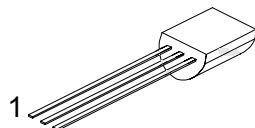


MPSA94*PNP EPITAXIAL SILICON TRANSISTOR***HIGH VOLTAGE TRANSISTOR****■ FEATURES**

- * Collector-Emitter voltage:
 $V_{CEO}=-400V$
- * Collector Dissipation:
 $P_{D(MAX)}=625mW$
- * Low collector-Emitter saturation voltage



SOT-89

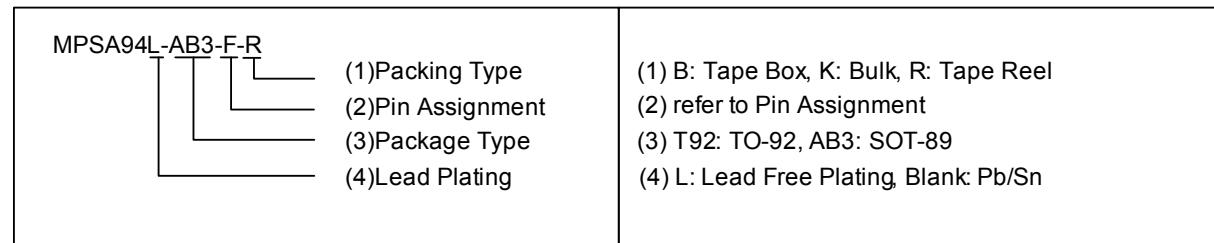


TO-92

*Pb-free plating product number: MPSA94L

■ ORDERING INFORMATION

Order Number		Package	Pin Assignment			Packing
Normal	Lead Free Plating		1	2	3	
MPSA94-AB3-F-R	MPSA94-AB3-F-R	SOT-89	B	C	E	Tape Reel
MPSA94-T92-C-B	MPSA94-T92-C-B	TO-92	E	B	C	Tape Box
MPSA94-T92-C-K	MPSA94-T92-C-K	TO-92	E	B	C	Bulk



■ **ABSOLUTE MAXIMUM RATING** (Operating temperature range applies unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Collector-Base Voltage	V _{CBO}	-400	V
Collector-Emitter Voltage	V _{CEO}	-400	V
Emitter-Base Voltage	V _{EBO}	-6	V
Collector Power Dissipation(Ta=25°C)	TO-92	625	mW
	SOT-89	0.5	W
Collector Current	I _C	-300	mA
Junction Temperature	T _J	+150	°C
Storage Temperature	T _{STG}	-40 ~ +150	°C

Note Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

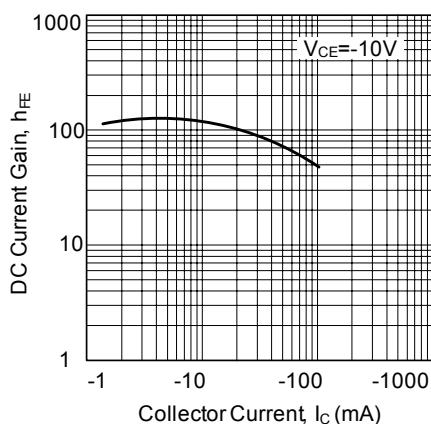
■ **ELECTRICAL CHARACTERISTICS** (T_J=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	BV _{CBO}	I _C =-100μA, I _E =0	-400			V
Collector-Emitter Breakdown Voltage	BV _{CEO}	I _C =-1mA, I _B =0	-400			V
Collector-Emitter Breakdown Voltage	BV _{CES}	I _C =-100μA, V _{BE} =0	-400			V
Emitter-Base Breakdown Voltage	BV _{EBO}	I _E =-100μA, I _C =0	-5			V
Collector Cut-off Current	I _{CBO}	V _{CB} =-300V, I _E =0			-100	nA
Collector Cut-off Current	I _{CES}	V _{CB} =-400V, V _{BE} =0			-1	μA
Emitter Cut-off Current	I _{EBO}	V _{EB} =-4V, I _C =0			100	nA
DC Current Gain(note)	h _{FE}	V _{CE} =-10V, I _C =-1mA	60			
		V _{CE} =-10V, I _C =-10mA	70		300	
		V _{CE} =-10V, I _C =-50mA	70			
		V _{CE} =-10V, I _C =-100mA	40			
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	I _C =-10mA, I _B =-1mA I _C =-50mA, I _B =-5mA			-0.20 -0.5	V
Base-Emitter Saturation Voltage	V _{BE(SAT)}	I _C =-10mA, I _B =-1mA			-0.75	V
Output Capacitance	C _{ob}	V _{CB} =-20V, I _E =0, f=1MHz			7	pF

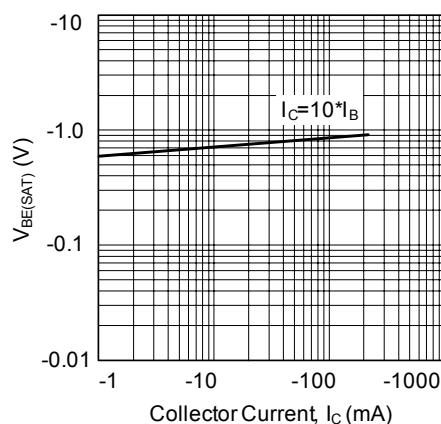
Note: Pulse test: PW<300μs, Duty Cycle<2%

■ TYPICAL CHARACTERISTICS

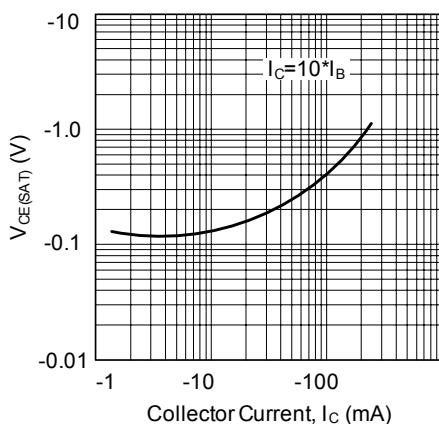
DC Current Gain



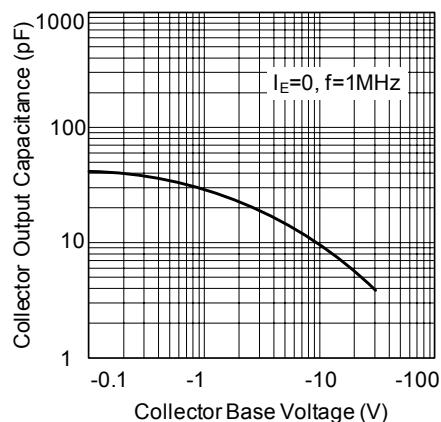
Base-Emitter Saturation Voltage



Collector-Emitter Saturation Voltage



Collector Output Capacitance



UTC assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all UTC products described or contained herein. UTC products are not designed for use in life support appliances, devices or systems where malfunction of these products can be reasonably expected to result in personal injury. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner. The information presented in this document does not form part of any quotation or contract, is believed to be accurate and reliable and may be changed without notice.